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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, I ² C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	DMA, I ² S, POR, PWM, WDT
Number of I/O	87
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	40K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 39x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f303vct7tr

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2 Description

The STM32F303xB/STM32F303xC family is based on the high-performance ARM® Cortex®-M4 32-bit RISC core with FPU operating at a frequency of up to 72 MHz, and embedding a floating point unit (FPU), a memory protection unit (MPU) and an embedded trace macrocell (ETM). The family incorporates high-speed embedded memories (up to 256 Kbytes of Flash memory, up to 40 Kbytes of SRAM) and an extensive range of enhanced I/Os and peripherals connected to two APB buses.

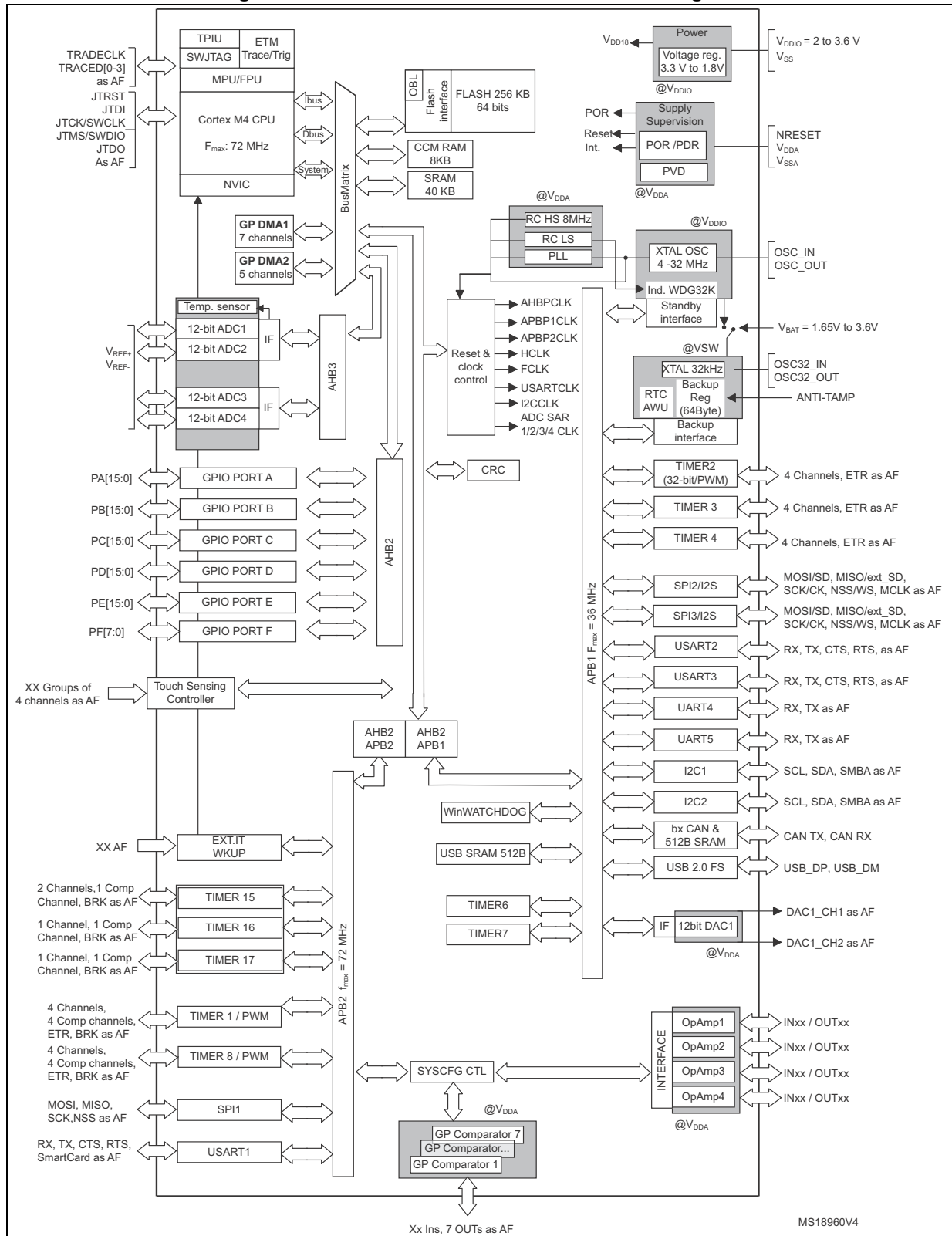
The devices offer up to four fast 12-bit ADCs (5 Msps), seven comparators, four operational amplifiers, up to two DAC channels, a low-power RTC, up to five general-purpose 16-bit timers, one general-purpose 32-bit timer, and two timers dedicated to motor control. They also feature standard and advanced communication interfaces: up to two I²Cs, up to three SPIs (two SPIs are with multiplexed full-duplex I2Ss), three USARTs, up to two UARTs, CAN and USB. To achieve audio class accuracy, the I2S peripherals can be clocked via an external PLL.

The STM32F303xB/STM32F303xC family operates in the -40 to +85 °C and -40 to +105 °C temperature ranges from a 2.0 to 3.6 V power supply. A comprehensive set of power-saving mode allows the design of low-power applications.

The STM32F303xB/STM32F303xC family offers devices in four packages ranging from 48 pins to 100 pins.

The set of included peripherals changes with the device chosen.

Figure 1. STM32F303xB/STM32F303xC block diagram



1. AF: alternate function on I/O pins.

3.16 Fast comparators (COMP)

The STM32F303xB/STM32F303xC devices embed seven fast rail-to-rail comparators with programmable reference voltage (internal or external), hysteresis and speed (low speed for low-power) and with selectable output polarity.

The reference voltage can be one of the following:

- External I/O
- DAC output pin
- Internal reference voltage or submultiple (1/4, 1/2, 3/4). Refer to [Table 28: Embedded internal reference voltage on page 62](#) for the value and precision of the internal reference voltage.

All comparators can wake up from STOP mode, generate interrupts and breaks for the timers and can be also combined per pair into a window comparator

3.17 Timers and watchdogs

The STM32F303xB/STM32F303xC includes two advanced control timers, up to six general-purpose timers, two basic timers, two watchdog timers and a SysTick timer. The table below compares the features of the advanced control, general purpose and basic timers.

Table 5. Timer feature comparison

Timer type	Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/compare Channels	Complementary outputs
Advanced	TIM1, TIM8	16-bit	Up, Down, Up/Down	Any integer between 1 and 65536	Yes	4	Yes
General-purpose	TIM2	32-bit	Up, Down, Up/Down	Any integer between 1 and 65536	Yes	4	No
General-purpose	TIM3, TIM4	16-bit	Up, Down, Up/Down	Any integer between 1 and 65536	Yes	4	No
General-purpose	TIM15	16-bit	Up	Any integer between 1 and 65536	Yes	2	1
General-purpose	TIM16, TIM17	16-bit	Up	Any integer between 1 and 65536	Yes	1	1
Basic	TIM6, TIM7	16-bit	Up	Any integer between 1 and 65536	Yes	0	No

Note: TIM1/8 can have PLL as clock source, and therefore can be clocked at 144 MHz.

Table 12. Legend/abbreviations used in the pinout table

Name		Abbreviation	Definition
Pin name		Unless otherwise specified in brackets below the pin name, the pin function during and after reset is the same as the actual pin name	
Pin type		S	Supply pin
		I	Input only pin
		I/O	Input / output pin
I/O structure		FT	5 V tolerant I/O
		FTf	5 V tolerant I/O, FM+ capable
		TTa	3.3 V tolerant I/O directly connected to ADC
		TC	Standard 3.3V I/O
		B	Dedicated BOOT0 pin
		RST	Bidirectional reset pin with embedded weak pull-up resistor
Notes		Unless otherwise specified by a note, all I/Os are set as floating inputs during and after reset	
Pin functions	Alternate functions	Functions selected through GPIOx_AFR registers	
	Additional functions	Functions directly selected/enabled through peripheral registers	

Table 13. STM32F303xB/STM32F303xC pin definitions

Pin number				Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
WLCSP100	LQFP100	LQFP64	LQFP48					Alternate functions	Additional functions
D6	1	-	-	PE2	I/O	FT	(1)	TRACECK, TIM3_CH1, TSC_G7_IO1, EVENTOUT	-
D7	2	-	-	PE3	I/O	FT	(1)	TRACED0, TIM3_CH2, TSC_G7_IO2, EVENTOUT	-
C8	3	-	-	PE4	I/O	FT	(1)	TRACED1, TIM3_CH3, TSC_G7_IO3, EVENTOUT	-
B9	4	-	-	PE5	I/O	FT	(1)	TRACED2, TIM3_CH4, TSC_G7_IO4, EVENTOUT	-
E7	5	-	-	PE6	I/O	FT	(1)	TRACED3, EVENTOUT	WKUP3, RTC_TAMP3
D8	6	1	1	V _{BAT}	S	-	-	Backup power supply	

Table 13. STM32F303xB/STM32F303xC pin definitions (continued)

Pin number				Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
WLCSP100	LQFP100	LQFP64	LQFP48					Alternate functions	Additional functions
F6	34	25	-	PC5	I/O	TTa	(1)	USART1_RX, TSC_G3_IO1, EVENTOUT	ADC2_IN11, OPAMP2_VINM, OPAMP1_VINM
J6	35	26	18	PB0	I/O	TTa	-	TIM3_CH3, TIM1_CH2N, TIM8_CH2N, TSC_G3_IO2, EVENTOUT	ADC3_IN12, COMP4_INP, OPAMP3_VINP, OPAMP2_VINP
K6	36	27	19	PB1	I/O	TTa	(4) (5)	TIM3_CH4, TIM1_CH3N, TIM8_CH3N, COMP4_OUT, TSC_G3_IO3, EVENTOUT	ADC3_IN1, OPAMP3_VOUT-
K5	37	28	20	PB2	I/O	TTa	-	TSC_G3_IO4, EVENTOUT	ADC2_IN12, COMP4_INM, OPAMP3_VINM
F8	38	-	-	PE7	I/O	TTa	(1)	TIM1_ETR, EVENTOUT	ADC3_IN13, COMP4_INP
E6	39	-	-	PE8	I/O	TTa	(1)	TIM1_CH1N, EVENTOUT	COMP4_INM, ADC34_IN6
-	40	-	-	PE9	I/O	TTa	(4) (1)	TIM1_CH1, EVENTOUT	ADC3_IN2
-	41	-	-	PE10	I/O	TTa	(1)	TIM1_CH2N, EVENTOUT	ADC3_IN14
H5	42	-	-	PE11	I/O	TTa	(1)	TIM1_CH2, EVENTOUT	ADC3_IN15
G5	43	-	-	PE12	I/O	TTa	(1)	TIM1_CH3N, EVENTOUT	ADC3_IN16
-	44	-	-	PE13	I/O	TTa	(1)	TIM1_CH3, EVENTOUT	ADC3_IN3
-	45	-	-	PE14	I/O	TTa	(4) (1)	TIM1_CH4, TIM1_BKIN2, EVENTOUT	ADC4_IN1
-	46	-	-	PE15	I/O	TTa	(4) (1)	USART3_RX, TIM1_BKIN, EVENTOUT	ADC4_IN2
K4	47	29	21	PB10	I/O	TTa	-	USART3_TX, TIM2_CH3, TSC_SYNC, EVENTOUT	COMP5_INM, OPAMP4_VINM, OPAMP3_VINM
K3	48	30	22	PB11	I/O	TTa	-	USART3_RX, TIM2_CH4, TSC_G6_IO1, EVENTOUT	COMP6_INP, OPAMP4_VINP
K1, J1, K2	49	31	23	VSS	S	-	-	Digital ground	
J5	50	32	24	VDD	S	-	-	Digital power supply	
J4	51	33	25	PB12	I/O	TTa	(4) (5)	SPI2_NSS, I2S2_WS, I2C2_SMB, USART3_CK, TIM1_BKIN, TSC_G6_IO2, EVENTOUT	ADC4_IN3, COMP3_INM, OPAMP4_VOUT

Table 13. STM32F303xB/STM32F303xC pin definitions (continued)

Pin number				Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
WLCSP100	LQFP100	LQFP64	LQFP48					Alternate functions	Additional functions
B2	77	50	38	PA15	I/O	FTf	-	I2C1_SCL, SPI1_NSS, SPI3_NSS, I2S3_WS, JTDI, USART2_RX, TIM1_BKIN, TIM2_CH1_ETR, TIM8_CH1, EVENTOUT	-
E4	78	51	-	PC10	I/O	FT	(1)	SPI3_SCK, I2S3_CK, USART3_TX, UART4_TX, TIM8_CH1N, EVENTOUT	-
D3	79	52	-	PC11	I/O	FT	(1)	SPI3_MISO, I2S3ext_SD, USART3_RX, UART4_RX, TIM8_CH2N, EVENTOUT	-
A3	80	53	-	PC12	I/O	FT	(1)	SPI3_MOSI, I2S3_SD, USART3_CK, UART5_TX, TIM8_CH3N, EVENTOUT	-
B3	81	-	-	PD0	I/O	FT	(1)	CAN_RX, EVENTOUT	-
C3	82	-	-	PD1	I/O	FT	(1)	CAN_TX, TIM8_CH4, TIM8_BKIN2, EVENTOUT	-
A4	83	54	-	PD2	I/O	FT	(1)	UART5_RX, TIM3_ETR, TIM8_BKIN, EVENTOUT	-
B4	84	-	-	PD3	I/O	FT	(1)	USART2_CTS, TIM2_CH1_ETR, EVENTOUT	-
C4	85	-	-	PD4	I/O	FT	(1)	USART2_RTS_DE, TIM2_CH2, EVENTOUT	-
-	86	-	-	PD5	I/O	FT	(1)	USART2_TX, EVENTOUT	-
-	87	-	-	PD6	I/O	FT	(1)	USART2_RX, TIM2_CH4, EVENTOUT	-
D4	88	-	-	PD7	I/O	FT	(1)	USART2_CK, TIM2_CH3, EVENTOUT	-
A5	89	55	39	PB3	I/O	FT	-	SPI3_SCK, I2S3_CK, SPI1_SCK, USART2_TX, TIM2_CH2, TIM3_ETR, TIM4_ETR, TIM8_CH1N, TSC_G5_IO1, JTDO- TRACESWO, EVENTOUT	-



Table 14. Alternate functions for port A

Port & Pin Name	AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF14	AF15
PA0	-	TIM2_CH1_ETR	-	TSC_G1_IO1	-	-	-	USART2_CTS	COMP1_OUT	TIM8_BKIN	TIM8_ETR	-	-	-	EVENT OUT
PA1	RTC_REFIN	TIM2_CH2	-	TSC_G1_IO2	-	-	-	USART2_RTS_DE		TIM15_CH1N	-	-	-	-	EVENT OUT
PA2	-	TIM2_CH3	-	TSC_G1_IO3	-	-	-	USART2_TX	COMP2_OUT	TIM15_CH1	-	-	-	-	EVENT OUT
PA3	-	TIM2_CH4	-	TSC_G1_IO4	-	-	-	USART2_RX	-	TIM15_CH2	-	-	-	-	EVENT OUT
PA4	-	-	TIM3_CH2	TSC_G2_IO1	-	SPI1_NSS	SPI3_NSS, I2S3_WS	USART2_CK	-	-	-	-	-	-	EVENT OUT
PA5	-	TIM2_CH1_ETR	-	TSC_G2_IO2	-	SPI1_SCK	-	-	-	-	-	-	-	-	EVENT OUT
PA6	-	TIM16_CH1	TIM3_CH1	TSC_G2_IO3	TIM8_BKIN	SPI1_MISO	TIM1_BKIN	-	COMP1_OUT	-	-	-	-	-	EVENT OUT
PA7	-	TIM17_CH1	TIM3_CH2	TSC_G2_IO4	TIM8_CH1N	SPI1_MOSI	TIM1_CH1N	-	COMP2_OUT	-	-	-	-	-	EVENT OUT
PA8	MCO	-	-	-	I2C2_SMBA	I2S2_MCK	TIM1_CH1	USART1_CK	COMP3_OUT	-	TIM4_ETR	-	-	-	EVENT OUT
PA9	-	-	-	TSC_G4_IO1	I2C2_SCL	I2S3_MCK	TIM1_CH2	USART1_TX	COMP5_OUT	TIM15_BKIN	TIM2_CH3	-	-	-	EVENT OUT
PA10	-	TIM17_BKIN	-	TSC_G4_IO2	I2C2_SDA	-	TIM1_CH3	USART1_RX	COMP6_OUT	-	TIM2_CH4	TIM8_BKIN	-	-	EVENT OUT
PA11	-	-	-	-	-	-	TIM1_CH1N	USART1_CTS	COMP1_OUT	CAN_RX	TIM4_CH1	TIM1_CH4	TIM1_BKIN2	USB_DM	EVENT OUT

Table 37. Switching output I/O current consumption

Symbol	Parameter	Conditions ⁽¹⁾	I/O toggling frequency (f _{SW})	Typ	Unit
I _{SW}	I/O current consumption	$V_{DD} = 3.3\text{ V}$ $C_{ext} = 0\text{ pF}$ $C = C_{INT} + C_{EXT} + C_S$	2 MHz	0.90	mA
			4 MHz	0.93	
			8 MHz	1.16	
			18 MHz	1.60	
			36 MHz	2.51	
			48 MHz	2.97	
		$V_{DD} = 3.3\text{ V}$ $C_{ext} = 10\text{ pF}$ $C = C_{INT} + C_{EXT} + C_S$	2 MHz	0.93	
			4 MHz	1.06	
			8 MHz	1.47	
			18 MHz	2.26	
			36 MHz	3.39	
			48 MHz	5.99	
		$V_{DD} = 3.3\text{ V}$ $C_{ext} = 22\text{ pF}$ $C = C_{INT} + C_{EXT} + C_S$	2 MHz	1.03	
			4 MHz	1.30	
			8 MHz	1.79	
			18 MHz	3.01	
			36 MHz	5.99	
		$V_{DD} = 3.3\text{ V}$ $C_{ext} = 33\text{ pF}$ $C = C_{INT} + C_{EXT} + C_S$	2 MHz	1.10	
			4 MHz	1.31	
			8 MHz	2.06	
			18 MHz	3.47	
			36 MHz	8.35	
		$V_{DD} = 3.3\text{ V}$ $C_{ext} = 47\text{ pF}$ $C = C_{INT} + C_{EXT} + C_S$	2 MHz	1.20	
			4 MHz	1.54	
			8 MHz	2.46	
			18 MHz	4.51	
			36 MHz	9.98	

1. CS = 5 pF (estimated value).

6.3.7 External clock source characteristics

High-speed external user clock generated from an external source

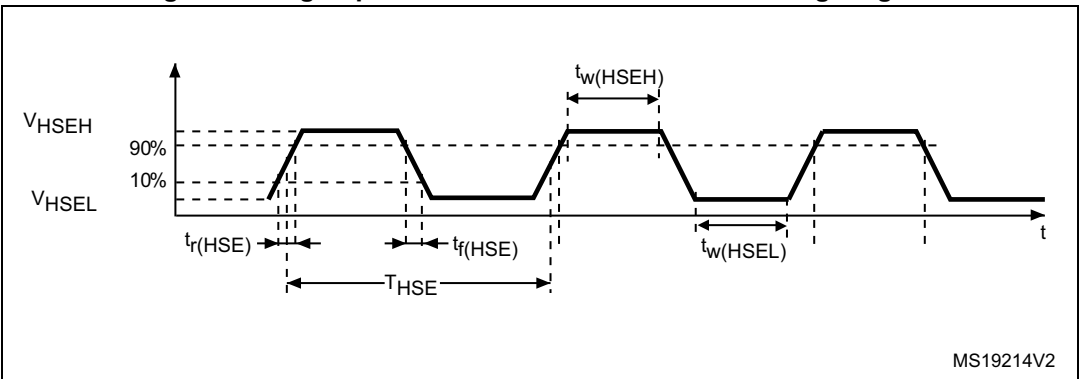
In bypass mode the HSE oscillator is switched off and the input pin is a standard GPIO. The external clock signal has to respect the I/O characteristics in [Section 6.3.14](#). However, the recommended clock input waveform is shown in [Figure 14](#).

Table 40. High-speed external user clock characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSE_ext}	User external clock source frequency ⁽¹⁾	-	1	8	32	MHz
V_{HSEH}	OSC_IN input pin high level voltage		$0.7V_{DD}$	-	V_{DD}	V
V_{HSEL}	OSC_IN input pin low level voltage		V_{SS}	-	$0.3V_{DD}$	
$t_{w(HSEH)}$ $t_{w(HSEL)}$	OSC_IN high or low time ⁽¹⁾		15	-	-	ns
$t_r(HSE)$ $t_f(HSE)$	OSC_IN rise or fall time ⁽¹⁾		-	-	20	

1. Guaranteed by design.

Figure 14. High-speed external clock source AC timing diagram



MS19214V2

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

Table 50. EMI characteristics

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. [f _{HSE} /f _{HCLK}]	Unit
				8/72 MHz	
S _{EMI}	Peak level	V _{DD} = 3.6 V, T _A = 25 °C, LQFP100 package compliant with IEC 61967-2	0.1 to 30 MHz	7	dBμV
			30 to 130 MHz	20	
			130 MHz to 1GHz	27	
			SAE EMI Level	4	-

6.3.12 Electrical sensitivity characteristics

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the JESD22-A114, ANSI/ESD STM5.3.1 standard.

Table 51. ESD absolute maximum ratings

Symbol	Ratings	Conditions		Class	Maximum value ⁽¹⁾	Unit
V _{ESD(HBM)}	Electrostatic discharge voltage (human body model)	T _A = +25 °C, conforming to JESD22-A114		2	2000	V
V _{ESD(CDM)}	Electrostatic discharge voltage (charge device model)	T _A = +25 °C, conforming to ANSI/ESD STM5.3.1	WLCSP100 package	3	250	
			Packages except WLCSP100	4	500	

1. Guaranteed by characterization results.

6.3.14 I/O port characteristics

General input/output characteristics

Unless otherwise specified, the parameters given in [Table 54](#) are derived from tests performed under the conditions summarized in [Table 24](#). All I/Os are CMOS and TTL compliant.

Table 54. I/O static characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IL}	Low level input voltage	TC and TTa I/O	-	-	$0.3 V_{DD} + 0.07^{(1)}$	V
		FT and FTf I/O	-	-	$0.475 V_{DD} - 0.2^{(1)}$	
		BOOT0	-	-	$0.3 V_{DD} - 0.3^{(1)}$	
		All I/Os except BOOT0	-	-	$0.3 V_{DD}^{(2)}$	
V_{IH}	High level input voltage	TC and TTa I/O	$0.445 V_{DD} + 0.398^{(1)}$	-	-	V
		FT and FTf I/O	$0.5 V_{DD} + 0.2^{(1)}$	-	-	
		BOOT0	$0.2 V_{DD} + 0.95^{(1)}$	-	-	
		All I/Os except BOOT0	$0.7 V_{DD}^{(2)}$	-	-	
V_{hys}	Schmitt trigger hysteresis	TC and TTa I/O	-	200 ⁽¹⁾	-	mV
		FT and FTf I/O	-	100 ⁽¹⁾	-	
		BOOT0	-	300 ⁽¹⁾	-	
I_{lkg}	Input leakage current ⁽³⁾	TC, FT and FTf I/O TTa I/O in digital mode $V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	± 0.1	μA
		TTa I/O in digital mode $V_{DD} \leq V_{IN} \leq V_{DDA}$	-	-	1	
		TTa I/O in analog mode $V_{SS} \leq V_{IN} \leq V_{DDA}$	-	-	± 0.2	
		FT and FTf I/O ⁽⁴⁾ $V_{DD} \leq V_{IN} \leq 5 V$	-	-	10	
R_{PU}	Weak pull-up equivalent resistor ⁽⁵⁾	$V_{IN} = V_{SS}$	25	40	55	$k\Omega$
R_{PD}	Weak pull-down equivalent resistor ⁽⁵⁾	$V_{IN} = V_{DD}$	25	40	55	$k\Omega$
C_{IO}	I/O pin capacitance	-	-	5	-	pF

1. Data based on design simulation.

2. Tested in production.

3. Leakage could be higher than the maximum value, if negative current is injected on adjacent pins. Refer to [Table 53: I/O current injection susceptibility](#).

4. To sustain a voltage higher than $V_{DD} + 0.3 V$, the internal pull-up/pull-down resistors must be disabled.

5. Pull-up and pull-down resistors are designed with a true resistance in series with a switchable PMOS/NMOS. This PMOS/NMOS contribution to the series resistance is minimum (~10% order).

Figure 21. Five volt tolerant (FT and FTf) I/O input characteristics - CMOS port

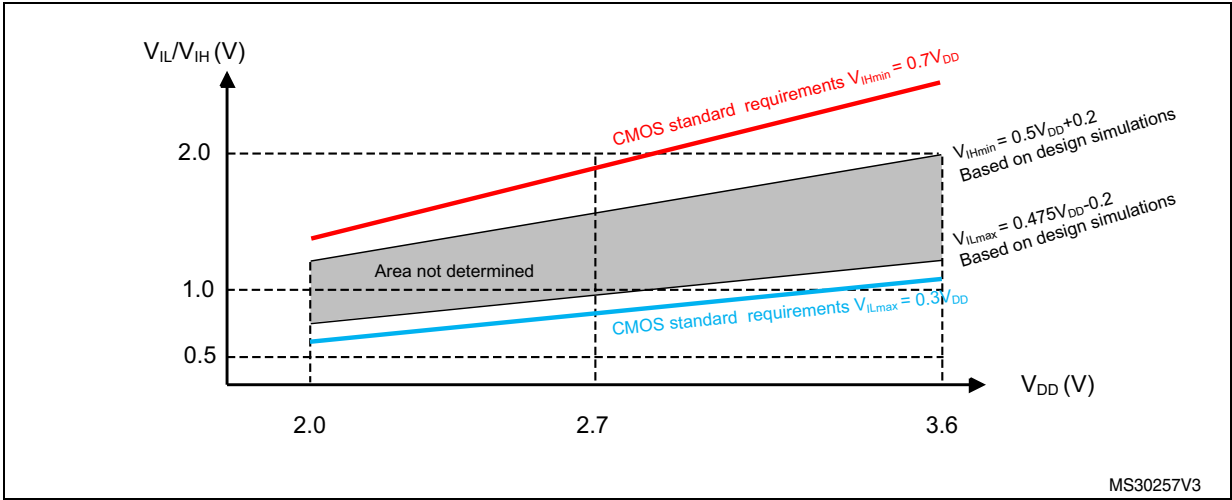
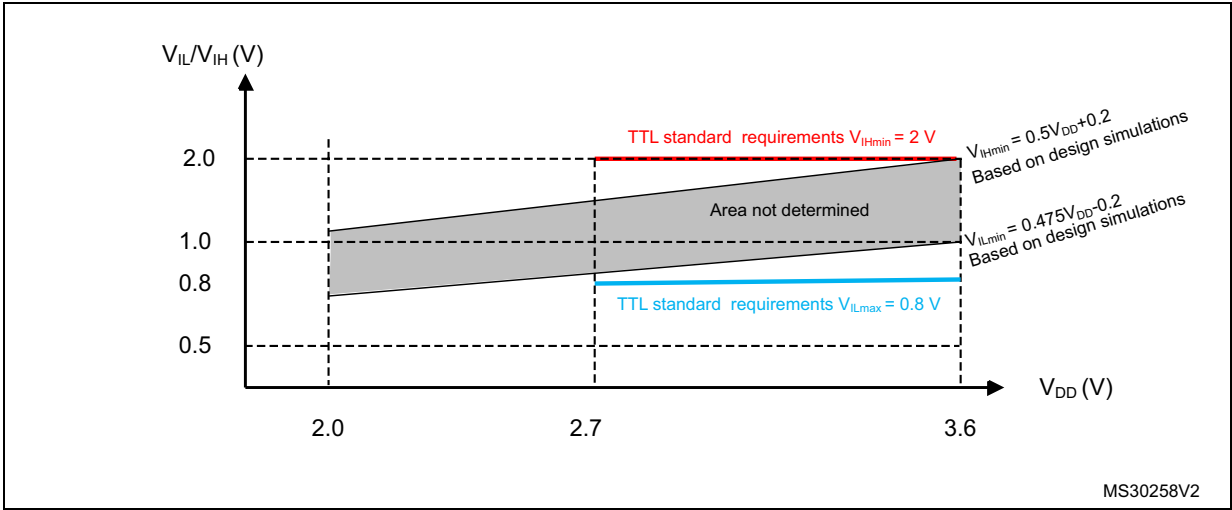


Figure 22. Five volt tolerant (FT and FTf) I/O input characteristics - TTL port



Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to ± 8 mA, and sink or source up to ± 20 mA (with a relaxed V_{OL}/V_{OH}).

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in [Section 6.2](#):

- The sum of the currents sourced by all the I/Os on V_{DD} , plus the maximum Run consumption of the MCU sourced on V_{DD} , cannot exceed the absolute maximum rating ΣI_{VDD} (see [Table 22](#)).
- The sum of the currents sunk by all the I/Os on V_{SS} plus the maximum Run consumption of the MCU sunk on V_{SS} cannot exceed the absolute maximum rating ΣI_{VSS} (see [Table 22](#)).

Output voltage levels

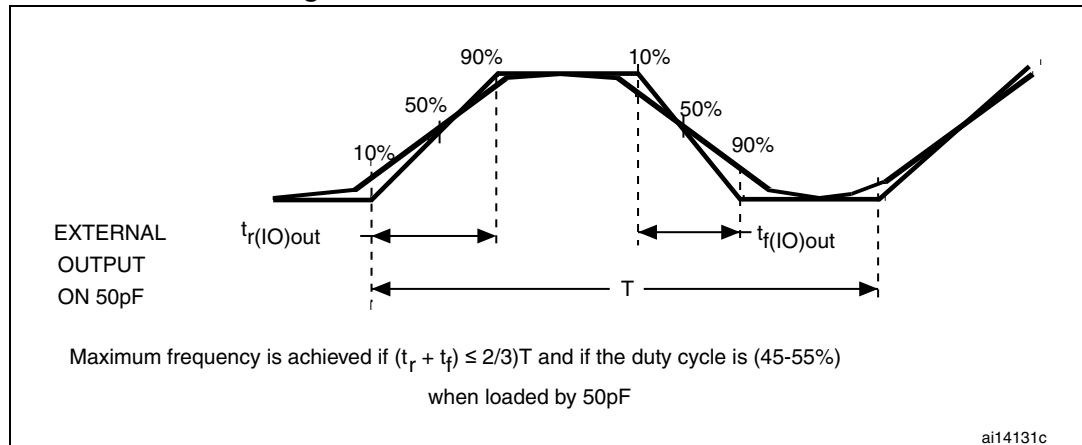
Unless otherwise specified, the parameters given in [Table 55](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 24](#). All I/Os (FT, TTA and TC unless otherwise specified) are CMOS and TTL compliant.

Table 55. Output voltage characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{OL}^{(1)}$	Output low level voltage for an I/O pin	CMOS port ⁽²⁾ $I_{IO} = +8$ mA $2.7\text{ V} < V_{DD} < 3.6\text{ V}$	-	0.4	V
$V_{OH}^{(3)}$	Output high level voltage for an I/O pin		$V_{DD}-0.4$	-	
$V_{OL}^{(1)}$	Output low level voltage for an I/O pin	TTL port ⁽²⁾ $I_{IO} = +8$ mA $2.7\text{ V} < V_{DD} < 3.6\text{ V}$	-	0.4	
$V_{OH}^{(3)}$	Output high level voltage for an I/O pin		2.4	-	
$V_{OL}^{(1)(4)}$	Output low level voltage for an I/O pin	$I_{IO} = +20$ mA $2.7\text{ V} < V_{DD} < 3.6\text{ V}$	-	1.3	
$V_{OH}^{(3)(4)}$	Output high level voltage for an I/O pin		$V_{DD}-1.3$	-	
$V_{OL}^{(1)(4)}$	Output low level voltage for an I/O pin	$I_{IO} = +6$ mA $2\text{ V} < V_{DD} < 2.7\text{ V}$	-	0.4	
$V_{OH}^{(3)(4)}$	Output high level voltage for an I/O pin		$V_{DD}-0.4$	-	
$V_{OLFM+}^{(1)(4)}$	Output low level voltage for an FTf I/O pin in FM+ mode	$I_{IO} = +20$ mA $2.7\text{ V} < V_{DD} < 3.6\text{ V}$	-	0.4	

1. The I_{IO} current sunk by the device must always respect the absolute maximum rating specified in [Table 22](#) and the sum of I_{IO} (I/O ports and control pins) must not exceed $\Sigma I_{IO(PIN)}$.
2. TTL and CMOS outputs are compatible with JEDEC standards JESD36 and JESD52.
3. The I_{IO} current sourced by the device must always respect the absolute maximum rating specified in [Table 22](#) and the sum of I_{IO} (I/O ports and control pins) must not exceed $\Sigma I_{IO(PIN)}$.
4. Data based on design simulation.

Figure 23. I/O AC characteristics definition



6.3.15 NRST pin characteristics

The NRST pin input driver uses CMOS technology. It is connected to a permanent pull-up resistor, R_{PU} (see [Table 54](#)).

Unless otherwise specified, the parameters given in [Table 57](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 24](#).

Table 57. NRST pin characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{IL(NRST)}^{(1)}$	NRST Input low level voltage	-	-	-	$0.3V_{DD} + 0.07^{(1)}$	V
$V_{IH(NRST)}^{(1)}$	NRST Input high level voltage	-	$0.445V_{DD} + 0.398^{(1)}$	-	-	
$V_{hys(NRST)}$	NRST Schmitt trigger voltage hysteresis	-	-	200	-	mV
R_{PU}	Weak pull-up equivalent resistor ⁽²⁾	$V_{IN} = V_{SS}$	25	40	55	k Ω
$V_{F(NRST)}^{(1)}$	NRST Input filtered pulse	-	-	-	$100^{(1)}$	ns
$V_{NF(NRST)}^{(1)}$	NRST Input not filtered pulse	-	$500^{(1)}$	-	-	ns

1. Guaranteed by design.

2. The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance must be minimum (~10% order).

Table 68. ADC characteristics (continued)

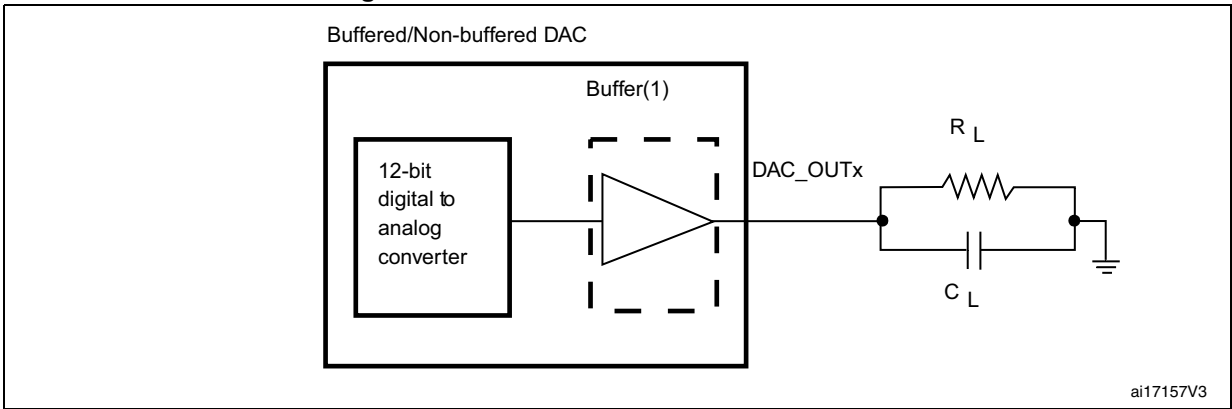
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{ADC}	ADC clock frequency	-	0.14	-	72	MHz
$f_{\text{S}}^{(1)}$	Sampling rate	Resolution = 12 bits, Fast Channel	0.01	-	5.14	MSPS
		Resolution = 10 bits, Fast Channel	0.012	-	6	
		Resolution = 8 bits, Fast Channel	0.014	-	7.2	
		Resolution = 6 bits, Fast Channel	0.0175	-	9	
$f_{\text{TRIG}}^{(1)}$	External trigger frequency	$f_{\text{ADC}} = 72 \text{ MHz}$ Resolution = 12 bits	-	-	5.14	MHz
		Resolution = 12 bits	-	-	14	$1/f_{\text{ADC}}$
V_{AIN}	Conversion voltage range ⁽²⁾	-	0	-	$V_{\text{REF+}}$	V
$R_{\text{AIN}}^{(1)}$	External input impedance	-	-	-	100	k Ω
$C_{\text{ADC}}^{(1)}$	Internal sample and hold capacitor	-	-	5	-	pF
$t_{\text{STAB}}^{(1)}$	Power-up time	-	1			conversion cycle
$t_{\text{CAL}}^{(1)}$	Calibration time	$f_{\text{ADC}} = 72 \text{ MHz}$	1.56			μs
		-	112			$1/f_{\text{ADC}}$
$t_{\text{latr}}^{(1)}$	Trigger conversion latency Regular and injected channels without conversion abort	CKMODE = 00	1.5	2	2.5	$1/f_{\text{ADC}}$
		CKMODE = 01	-	-	2	$1/f_{\text{ADC}}$
		CKMODE = 10	-	-	2.25	$1/f_{\text{ADC}}$
		CKMODE = 11	-	-	2.125	$1/f_{\text{ADC}}$
$t_{\text{latrinj}}^{(1)}$	Trigger conversion latency Injected channels aborting a regular conversion	CKMODE = 00	2.5	3	3.5	$1/f_{\text{ADC}}$
		CKMODE = 01	-	-	3	$1/f_{\text{ADC}}$
		CKMODE = 10	-	-	3.25	$1/f_{\text{ADC}}$
		CKMODE = 11	-	-	3.125	$1/f_{\text{ADC}}$

Table 75. DAC characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{\text{WAKEUP}}^{(3)}$	Wakeup time from off state (Setting the ENx bit in the DAC Control register)	$C_{\text{LOAD}} \leq 50 \text{ pF}$, $R_{\text{LOAD}} \geq 5 \text{ k}\Omega$	-	6.5	10	μs
PSRR+ ⁽¹⁾	Power supply rejection ratio (to V_{DDA}) (static DC measurement)	$C_{\text{LOAD}} = 50 \text{ pF}$, No $R_{\text{LOAD}} \geq 5 \text{ k}\Omega$	-	-67	-40	dB

1. Guaranteed by design.
2. Quiescent mode refers to the state of the DAC a keeping steady value on the output, so no dynamic consumption is involved.
3. Guaranteed by characterization results.

Figure 36. 12-bit buffered /non-buffered DAC



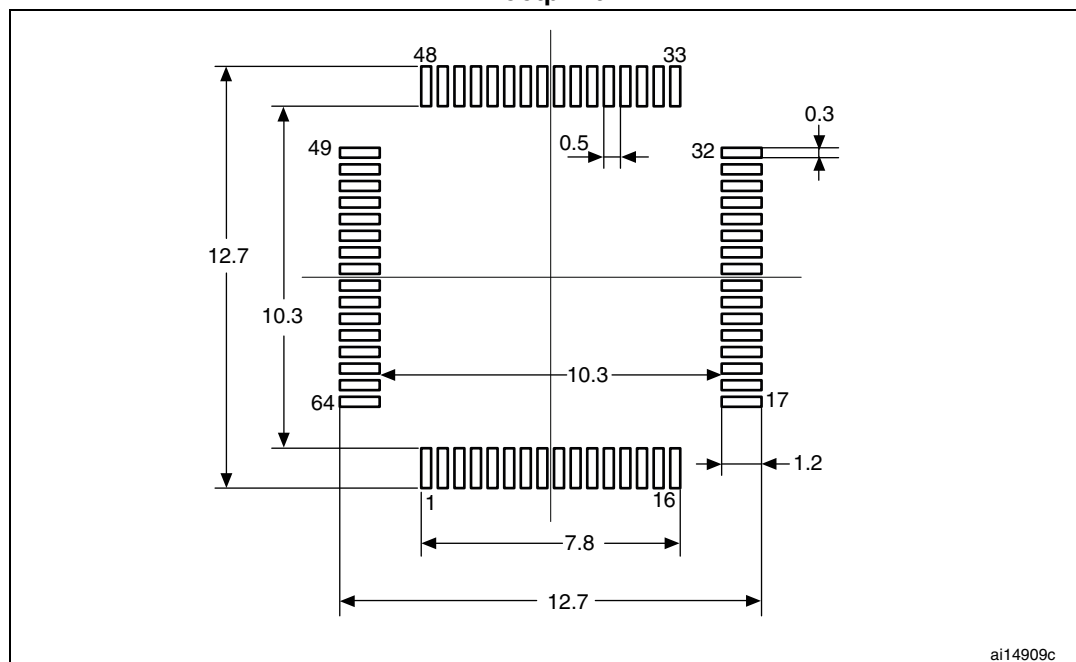
1. The DAC integrates an output buffer that can be used to reduce the output impedance and to drive external loads directly without the use of an external operational amplifier. The buffer can be bypassed by configuring the BOFFx bit in the DAC_CR register.

Table 82. LQFP64 – 10 x 10 mm, low-profile quad flat package mechanical data (continued)

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
E1	-	10.00	-	-	0.3937	-
E3	-	7.50	-	-	0.2953	-
e	-	0.50	-	-	0.0197	-
K	0°	3.5°	7°	0°	3.5°	7°
L	0.45	0.60	0.75	0.0177	0.0236	0.0295
L1	-	1.00	-	-	0.0394	-
ccc	-	-	0.08	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 43. LQFP64 – 10 x 10 mm, low-profile quad flat package recommended footprint



1. Dimensions are in millimeters.

Table 88. Document revision history (continued)

Date	Revision	Changes
05-Dec-2012	4	Updated first page Removed references to VDDSDx and VSSSD Added reference to PM0214 in Section 1 Moved Temp. sensor calibration values to Table 79 and VREF calibration values to Table 29 Updated Table 3: STM32F303xx family device features and peripheral counts Updated Section 3.4: Embedded SRAM Updated Section 3.2: Memory protection unit (MPU) Updated Section 3.24: Universal serial bus (USB) Modified Section 3.26: Touch sensing controller (TSC) Updated heading of Table 11: USART features Updated Table 16: STM32F302xB/STM32F302xC pin definitions Added notes to PC13, PC14 and PC15 in Table 16: STM32F302xB/STM32F302xC pin definitions Updated Figure 11: Power supply scheme Modified Table 21: Voltage characteristics Modified Table 22: Current characteristics Modified Table 24: General operating conditions Modified Figure 13: Typical VBAT current consumption (LSE and RTC ON/LSERDV[1:0] = '00') Updated Section 6.3.14: I/O port characteristics Updated Table 30: Typical and maximum current consumption from VDD supply at VDD = 3.6V and Table 31: Typical and maximum current consumption from the VDDA supply Updated Table 32: Typical and maximum VDD consumption in Stop and Standby modes and Table 33: Typical and maximum VDDA consumption in Stop and Standby modes Updated Table 34: Typical and maximum current consumption from VBAT supply Added Figure 13: Typical VBAT current consumption (LSE and RTC ON/LSERDV[1:0] = '00') Updated Table 35: Typical current consumption in Run mode, code with data processing running from Flash and Table 36: Typical current consumption in Sleep mode, code running from Flash or RAM Added Table 38: Peripheral current consumption Added Table 37: Switching output I/O current consumption Updated Section 6.3.6: Wakeup time from low-power mode Modified ESD absolute maximum ratings Modified Table 55: Output voltage characteristics Updated EMI characteristics Updated Table 56: I/O AC characteristics Updated Table 53: I/O current injection susceptibility Updated Table 58: TIMx characteristics Updated Section 7.4: WLCSP100 - 0.4 mm pitch wafer level chip scale package information Added Table 69: Maximum ADC RAIN Added Table 70: ADC accuracy - limited test conditions, 100-pin packages Updated Table 64: ADC accuracy - limited test conditions 2) Updated Table 75: DAC characteristics Updated Table 77: Operational amplifier characteristics Updated figures and tables in Section 7: Package information